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## 2SD1295

### Silicon NPN epitaxial planar type

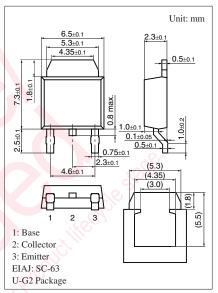
For low-frequency output amplification Complementary to 2SB0968

#### ■ Features

- Possible to solder radiation fin directly to printed circuit board
- Output of 4 W can be obtained by a complementary pair with 2SB0968

#### ■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

| Parameter                             | Symbol           | Rating      | Unit |
|---------------------------------------|------------------|-------------|------|
| Collector-base voltage (Emitter open) | $V_{CBO}$        | 50          | V    |
| Collector-emitter voltage (Base open) | V <sub>CEO</sub> | 40          | V    |
| Emitter-base voltage (Collector open) | $V_{EBO}$        | 5           | V    |
| Collector current                     | $I_{C}$          | 1.5         | A    |
| Peak collector current                | $I_{CP}$         | 3           | A    |
| Collector power dissipation           | P <sub>C</sub>   | 10          | W    |
| Junction temperature                  | T <sub>j</sub>   | 150         | °C   |
| Storage temperature                   | $T_{stg}$        | -55 to +150 | °C   |



Note) Self-supported type package is also prepared.

#### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

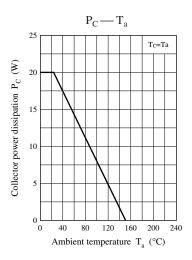
| Parameter                                    | Symbol               | Conditions  | Min | Тур | Max | Unit |
|--|----------------------|---|-----|-----|-----|------|
| Collector-base voltage (Emiter open)         | $V_{CBO}$            | $I_C = 1 \text{ mA}, I_E = 0$                                       | 50  | 0   |     | V    |
| Collector-emitter voltage (Base open)        | $V_{CEO}$            | $I_C = 2 \text{ mA}, I_B = 0$                                       | 40  |     |     | V    |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$            | $V_{CB} = 20 \text{ V}, I_{E} = 0$                                  |     |     | 1   | μΑ   |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$            | $V_{CE} = 10 \text{ V}, I_{B} = 0$                                  |     |     | 100 | μΑ   |
| Emiter-base cutoff current (Collector open)  | $I_{EBO}$            | $V_{EB} = 5 \text{ V}, I_{C} = 0$                                   |     |     | 10  | μΑ   |
| Forward current transfer ratio *             | h <sub>FE</sub>      | $V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$                         | 80  |     | 220 | _    |
| Collector-emitter saturation voltage         | V <sub>CE(sat)</sub> | $I_C = 1.5 \text{ A}, I_B = 0.15 \text{ A}$                         |     |     | 1   | V    |
| Base-emitter saturation voltage              | V <sub>BE(sat)</sub> | $I_C = 2 A, I_B = 0.2 A$  |     |     | 1.5 | V    |
| Transition frequency                         | $f_T$                | $V_{CE} = 5 \text{ V}, I_{C} = -0.5 \text{ A}, f = 200 \text{ MHz}$ |     | 150 |     | MHz  |
| Collector output capacitance                 | C <sub>ob</sub>      | $V_{CB} = 20 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$               |     | 35  |     | pF   |
| (Common base, input open circuited)          |                      |   |     |     |     |      |

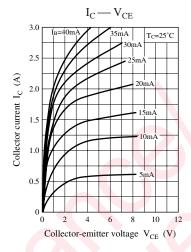
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

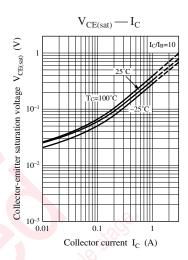
#### 2. \*: Rank classification

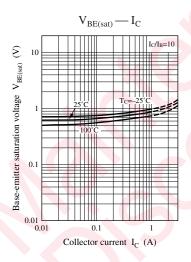
| Rank     | R         | S          |
|----------|-----------|------------|
| $h_{FE}$ | 80 to 160 | 120 to 220 |

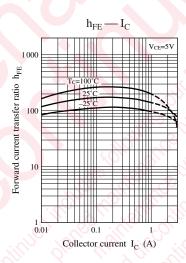
### **Panasonic**

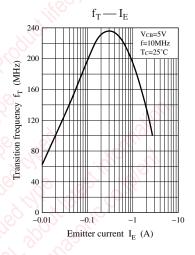


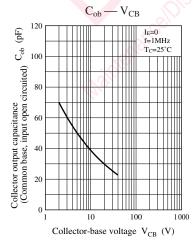


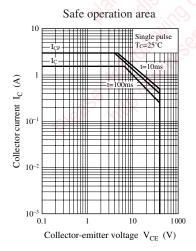




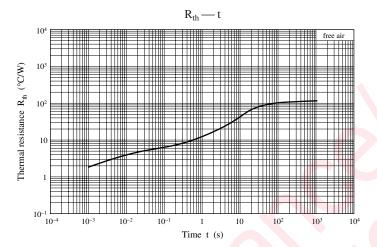








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